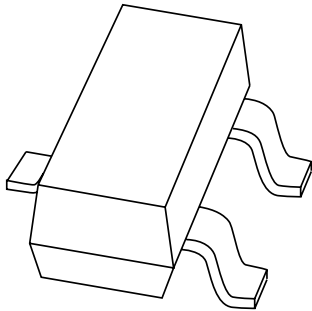


# DATA SHEET



## **BSR19; BSR19A** NPN high voltage transistors

Product data sheet  
Supersedes data of 2004 Jan 13

2004 Mar 15

# NPN high voltage transistors

# BSR19; BSR19A

### FEATURES

- Low current (max. 300 mA)
- High voltage (max. 160 V).

### APPLICATIONS

- General purpose switching and amplification
- Especially used for telephony applications.

### DESCRIPTION

NPN high-voltage transistor in a SOT23 plastic package.  
PNP complements: BSR20 and BSR20A.

### MARKING

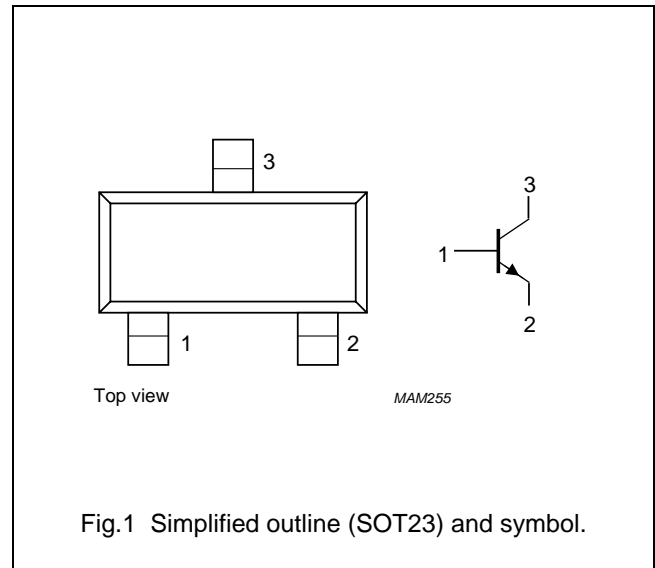
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BSR19	56* or U35
BSR19A	57* or U36

### Note

- \* = p : Made in Hong Kong.  
\* = t : Made in Malaysia.  
\* = W : Made in China.

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BSR19	–	plastic surface mounted package; 3 leads	SOT23
BSR19A	–	plastic surface mounted package; 3 leads	SOT23

## NPN high voltage transistors

## BSR19; BSR19A

## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BSR19		–	160	V
	BSR19A		–	180	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BSR19		–	140	V
	BSR19A		–	160	V
I <sub>CM</sub>	peak collector current		–	600	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	–	250	mW
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V			
	BSR19		60	–	
	BSR19A		80	–	
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 10 V; f = 100 MHz	100	300	MHz

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BSR19		–	160	V
	BSR19A		–	180	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BSR19		–	140	V
	BSR19A		–	160	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	6	V
I <sub>C</sub>	collector current (DC)		–	300	mA
I <sub>CM</sub>	peak collector current		–	600	mA
I <sub>B</sub>	base current (DC)		–	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	–	250	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W

## Note

1. Transistor mounted on an FR4 printed-circuit board.

## NPN high voltage transistors

## BSR19; BSR19A

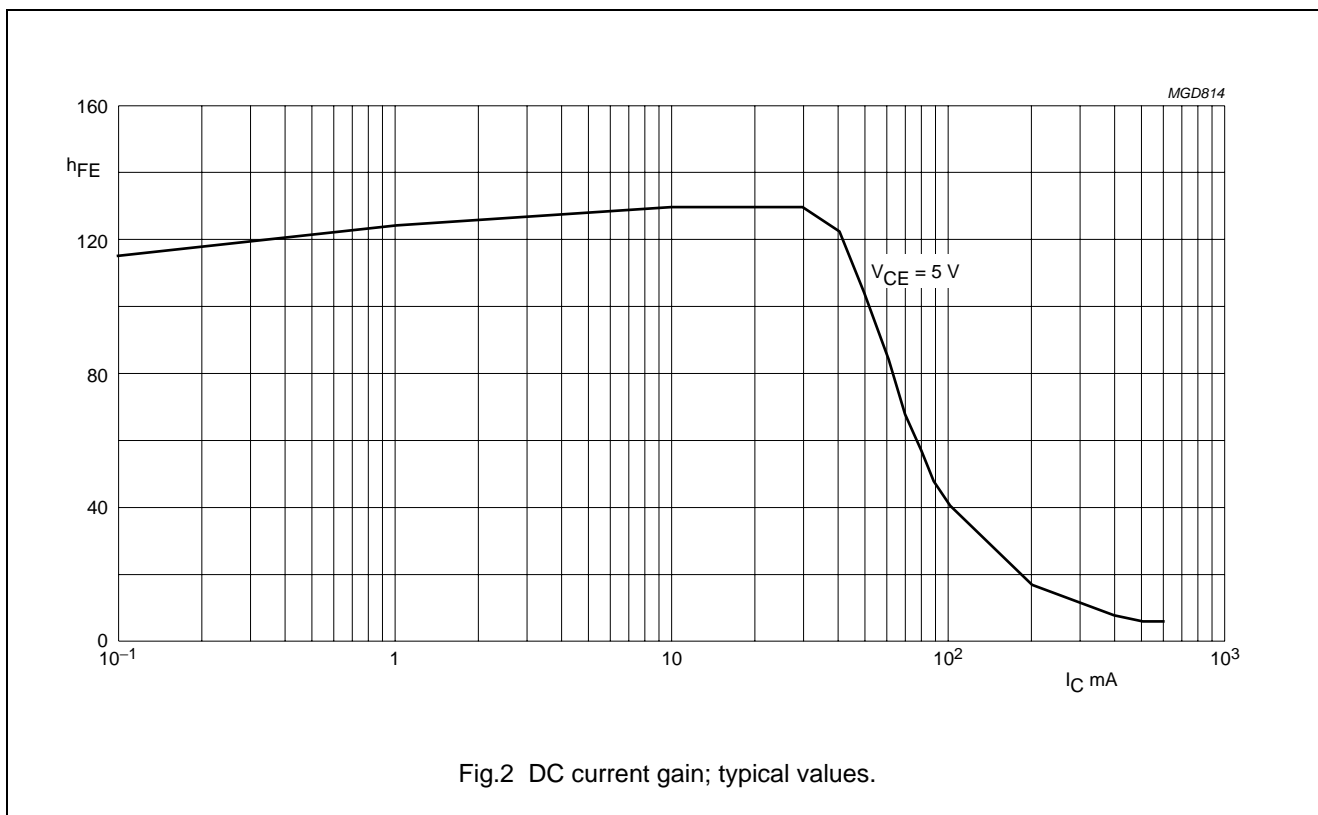
**CHARACTERISTICS**

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current BSR19	$I_E = 0\text{ A}; V_{CB} = 100\text{ V}$	–	100	nA
		$I_E = 0\text{ A}; V_{CB} = 100\text{ V}; T_{amb} = 100\text{ °C}$	–	100	$\mu\text{A}$
$I_{CBO}$	collector cut-off current BSR19A	$I_E = 0\text{ A}; V_{CB} = 120\text{ V}$	–	50	nA
		$I_E = 0\text{ A}; V_{CB} = 120\text{ V}; T_{amb} = 100\text{ °C}$	–	50	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0\text{ A}; V_{EB} = 4\text{ V}$	–	50	nA
$h_{FE}$	DC current gain BSR19 BSR19A	$I_C = 1\text{ mA}; V_{CE} = 5\text{ V}$	60	–	
			80	–	
	DC current gain BSR19 BSR19A	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	60	250	
			80	250	
	DC current gain BSR19 BSR19A	$I_C = 50\text{ mA}; V_{CE} = 5\text{ V}$	20	–	
			30	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	–	150	mV
$V_{CEsat}$	collector-emitter saturation voltage BSR19 BSR19A	$I_C = 50\text{ mA}; I_B = 5\text{ mA}$	–	250	mV
			–	200	mV
$C_c$	collector capacitance	$I_E = 0\text{ A}; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	6	pF
$f_T$	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	100	300	MHz

NPN high voltage transistors

BSR19; BSR19A



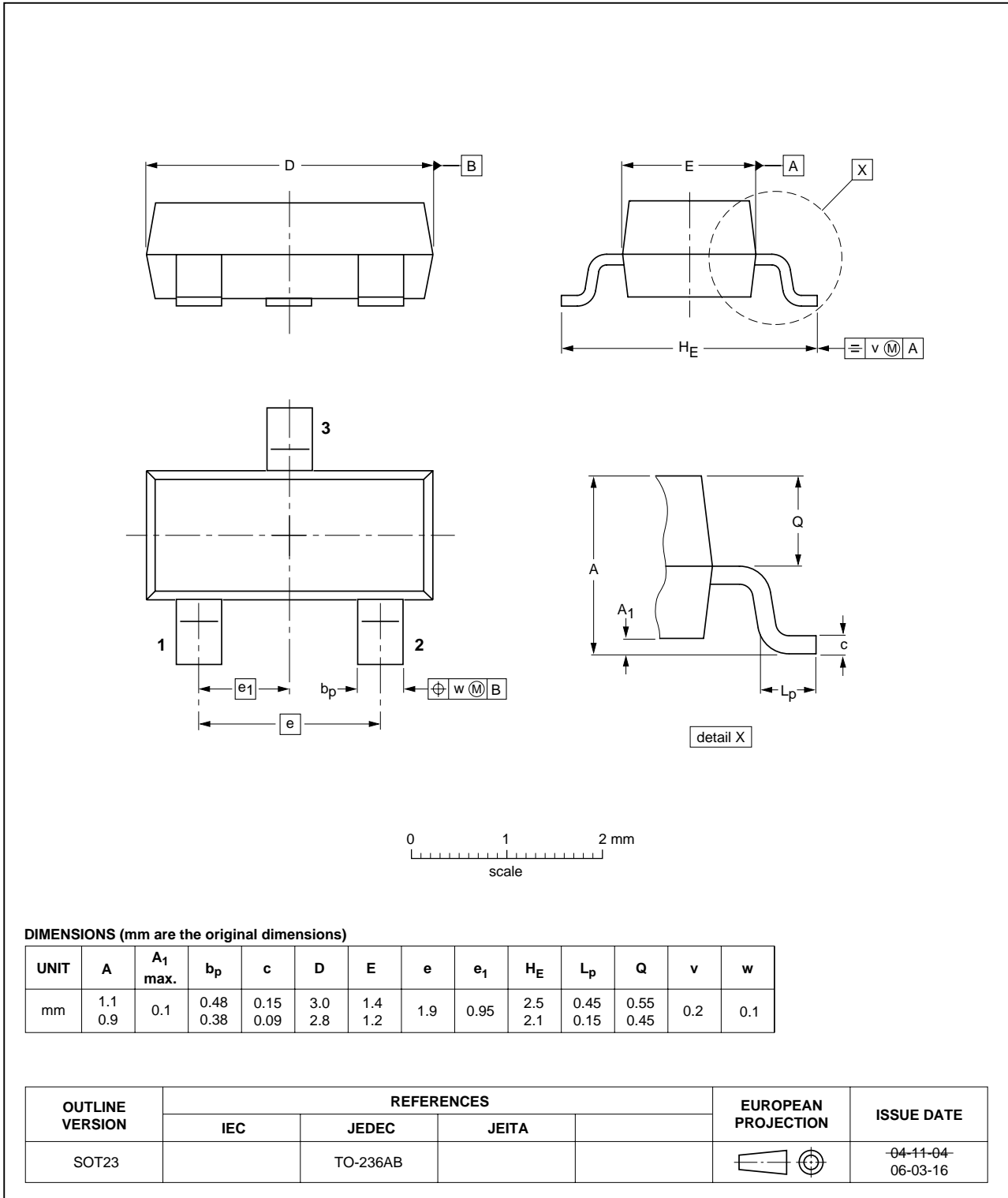
NPN high voltage transistors

BSR19; BSR19A

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



## NPN high voltage transistors

## BSR19; BSR19A

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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# ***NXP Semiconductors***

## **Customer notification**

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## **Contact information**

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